Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	300
Number of Gates	1000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p1000l-1fgg484

Introduction

Contents

This user's guide contains information to help designers understand and use Microsemi's ProASIC®3L devices. Each chapter addresses a specific topic. Most of these chapters apply to other Microsemi device families as well. When a feature or description applies only to a specific device family, this is made clear in the text.

Revision History

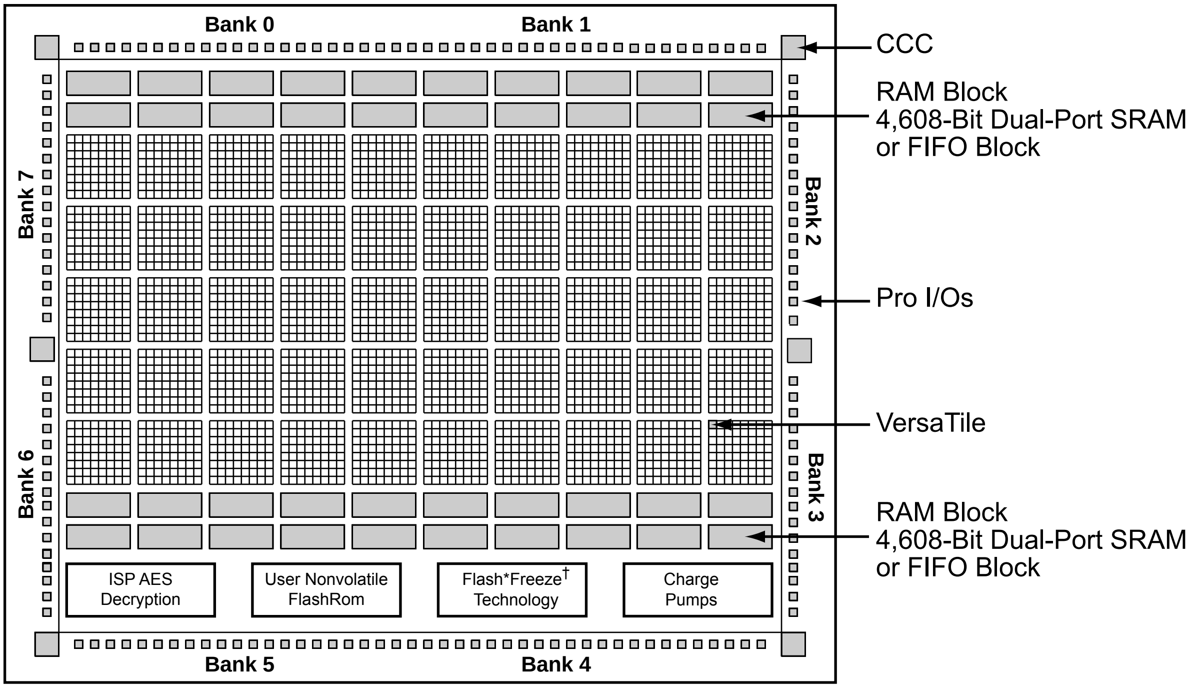
The revision history for each chapter is listed at the end of the chapter. Most of these chapters were formerly included in device handbooks. Some were originally application notes or information included in device datasheets.

A "Summary of Changes" table at the end of this user's guide lists the chapters that were changed in each revision of the document, with links to the "List of Changes" sections for those chapters.

Related Information

Refer to the *ProASIC3L Flash Family FPGAs* datasheet for detailed specifications, timing, and package and pin information.

The website page for ProASIC3L devices is /www.microsemi.com/soc/products/pa3l/default.aspx.



*Note: Flash*Freeze technology only applies to IGLOOe devices.*

Figure 1-7 • **IGLOOe and ProASIC3E Device Architecture Overview (AGLE600 device is shown)**

I/O State of Newly Shipped Devices

Devices are shipped from the factory with a test design in the device. The power-on switch for VCC is OFF by default in this test design, so I/Os are tristated by default. Tristated means the I/O is not actively driven and floats. The exact value cannot be guaranteed when it is floating. Even in simulation software, a tristate value is marked as unknown. Due to process variations and shifts, tristated I/Os may float toward High or Low, depending on the particular device and leakage level.

If there is concern regarding the exact state of unused I/Os, weak pull-up/pull-down should be added to the floating I/Os so their state is controlled and stabilized.

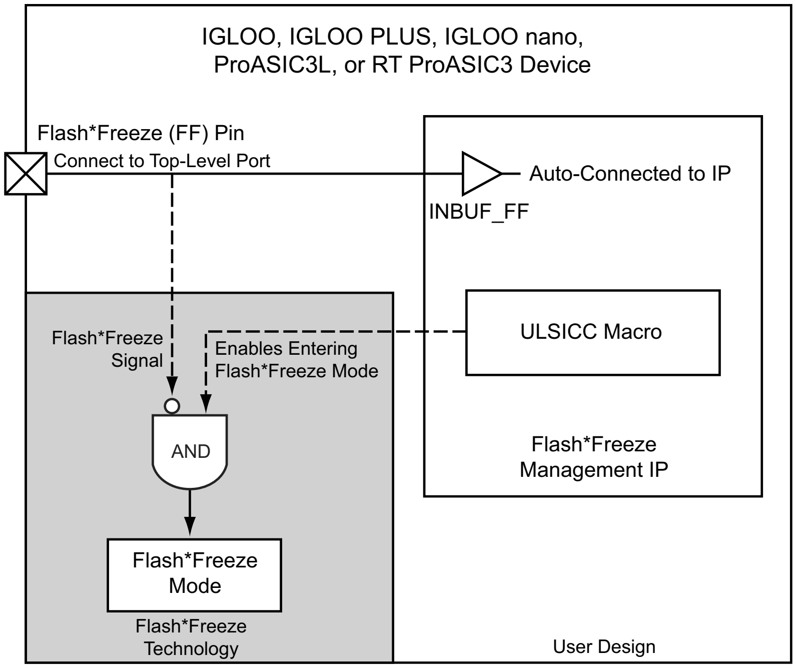


Figure 2-3 **• Flash*Freeze Mode Type 2 – Controlled by Flash*Freeze Pin and Internal Logic (LSICC signal)**

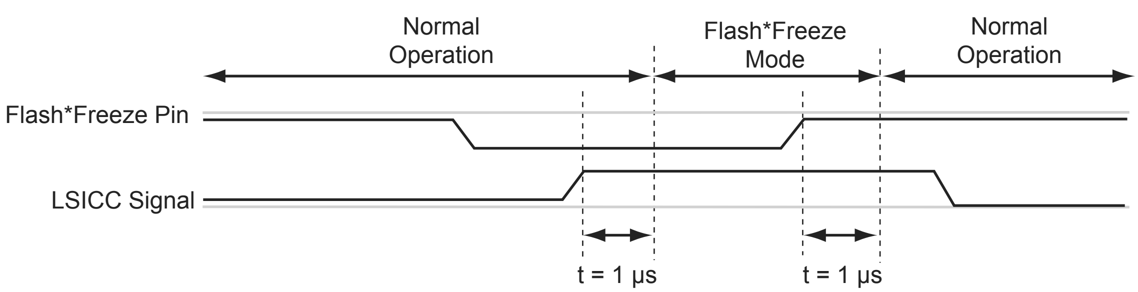


Figure 2-4 **• Flash*Freeze Mode Type 2 – Timing Diagram**

- There will be added skew and clock insertion delay due to the clock gating circuit. The user should analyze external setup/hold times carefully. The user should also ensure the additional skew across the clock gating filter circuit is accounted for in any paths where the launch register is driven from the filter input clock and captured by a register driven by the gated clock filter output clock.

Power Analysis

SmartPower identifies static and dynamic power consumption problems quickly within a design. It provides a hierarchical view, allowing users to drill down and estimate the power consumption of individual components or events. SmartPower analyzes power consumption for nets, gates, I/Os, memories, clocks, cores, clock domains, power supply rails, peak power during a clock cycle, and switching transitions.

SmartPower generates detailed hierarchical reports of the dynamic power consumption of a design for easy inspection. These reports include design-level power summary, average switching activity, and ambient and junction temperature readings. Enter the target clock and data frequencies for a design, and let SmartPower perform a detailed and accurate power analysis. SmartPower supports importing files in the VCD (Value-Change Dump) format as specified in the IEEE 1364 standard. It also supports the Synopsys® Switching Activity Interchange Format (SAIF) standard. Support for these formats lets designers generate switching activity information in a variety of simulators and then import this information directly into SmartPower.

For portable or battery-operated applications, a power profile feature enables you to measure power and battery life, based on a sequence of operational modes of the design. In most portable and battery-operated applications, the system is seldom fully "on" 100 percent of the time. "On" is a combination of fully active, standby, sleep, or other functional modes. SmartPower allows users to create a power profile for a design by specifying operational modes and the percent of time the device will run in each of the modes. Power is calculated for each of the modes, and total power is calculated based on the weighted average of all modes.

SmartPower also provides an estimated battery life based on the power profile. The current capacity for a given battery is entered and used to estimate the life of the battery. The result is an accurate and realistic indication of battery life.

More information on SmartPower can be found on the Microsemi SoC Products Group website:
http://www.microsemi.com/soc/products/software/libero/smartpower.aspx.

Additional Power Conservation Techniques

IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 FPGAs provide many ways to inherently conserve power; however, there are also several design techniques that can be used to reduce power on the board.

- Microsemi recommends that the designer use the minimum number of I/O banks possible and tie any unused power supplies (such as V_{CCPLL}, V_{CCI}, VMV, and V_{PUMP}) to ground.
- Leave unused I/O ports floating. Unused I/Os are configured by the software as follows:
  – Output buffer is disabled (with tristate value of high impedance)
  – Input buffer is disabled (with tristate value of high impedance)
- Use the lowest available voltage I/O standard, the lowest drive strength, and the slowest slew rate to reduce I/O switching contribution to power consumption.
- Advanced and pro I/O banks may consume slightly higher static current than standard and standard plus banks—avoid using advanced and pro banks whenever practical.
  – The small static power benefit obtained by avoiding advanced or pro I/O banks is usually negligible compared to the benefit of using a low power I/O standard.
- Deselect RAM blocks that are not being used.
- Only enable read and write ports on RAM blocks when they are needed.
- Gating clocks LOW offers improved static power of RAM blocks.
- Drive the FF port of RAM blocks with the Flash_Freeze_Enabled signal from the Flash*Freeze management IP.
- Drive inputs to the full voltage level so that all transistors are turned on or off completely.

3 – Global Resources in Low Power Flash Devices

Introduction

IGLOO, Fusion, and ProASIC3 FPGA devices offer a powerful, low-delay VersaNet global network scheme and have extensive support for multiple clock domains. In addition to the Clock Conditioning Circuits (CCCs) and phase-locked loops (PLLs), there is a comprehensive global clock distribution network called a VersaNet global network. Each logical element (VersaTile) input and output port has access to these global networks. The VersaNet global networks can be used to distribute low-skew clock signals or high-fanout nets. In addition, these highly segmented VersaNet global networks contain spines (the vertical branches of the global network tree) and ribs that can reach all the VersaTiles inside their region. This allows users the flexibility to create low-skew local clock networks using spines. This document describes VersaNet global networks and discusses how to assign signals to these global networks and spines in a design flow. Details concerning low power flash device PLLs are described in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" section on page 77. This chapter describes the low power flash devices' global architecture and uses of these global networks in designs.

Global Architecture

Low power flash devices offer powerful and flexible control of circuit timing through the use of global circuitry. Each chip has up to six CCCs, some with PLLs.

- In IGLOOe, ProASIC3EL, and ProASIC3E devices, all CCCs have PLLs—hence, 6 PLLs per device (except the PQ208 package, which has only 2 PLLs).
- In IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3, and ProASIC3L devices, the west CCC contains a PLL core (except in 10 k through 30 k devices).
- In Fusion devices, the west CCC also contains a PLL core. In the two larger devices (AFS600 and AFS1500), the west and east CCCs each contain a PLL.

Refer to Table 4-6 on page 100 for details. Each PLL includes delay lines, a phase shifter (0°, 90°, 180°, 270°), and clock multipliers/dividers. Each CCC has all the circuitry needed for the selection and interconnection of inputs to the VersaNet global network. The east and west CCCs each have access to three chip global lines on each side of the chip (six chip global lines total). The CCCs at the four corners each have access to three quadrant global lines in each quadrant of the chip (except in 10 k through 30 k gate devices).

The nano 10 k, 15 k, and 20 k devices support four VersaNet global resources, and 30 k devices support six global resources. The 10 k through 30 k devices have simplified CCCs called CCC-GLs.

The flexible use of the VersaNet global network allows the designer to address several design requirements. User applications that are clock-resource-intensive can easily route external or gated internal clocks using VersaNet global routing networks. Designers can also drastically reduce delay penalties and minimize resource usage by mapping critical, high-fanout nets to the VersaNet global network.

Note: Microsemi recommends that you choose the appropriate global pin and use the appropriate global resource so you can realize these benefits.

The following sections give an overview of the VersaNet global network, the structure of the global network, access point for the global networks, and the clock aggregation feature that enables a design to have very low clock skew using spines.

CCC Locations

CCCs located in the middle of the east and west sides of the device access the three VersaNet global networks on each side (six total networks), while the four CCCs located in the four corners access three quadrant global networks (twelve total networks). See Figure 4-13.

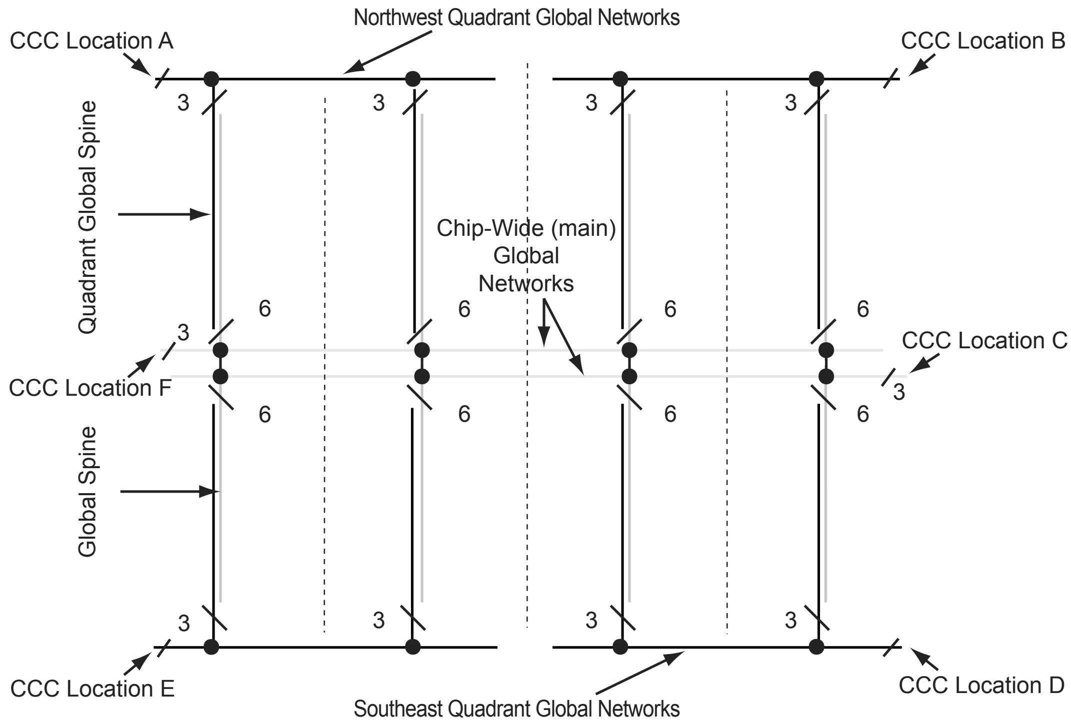


***Figure 4-13* • Global Network Architecture for 60 k Gate Devices and Above**

The following explains the locations of the CCCs in IGLOO and ProASIC3 devices:

In Figure 4-15 on page 98 through Figure 4-16 on page 98, CCCs with integrated PLLs are indicated in red, and simplified CCCs are indicated in yellow. There is a letter associated with each location of the CCC, in clockwise order. The upper left corner CCC is named "A," the upper right is named "B," and so on. These names finish up at the middle left with letter "F."

Each group of control bits is assigned a specific location in the configuration shift register. For a list of the 81 configuration bits (C[80:0]) in the CCC and a description of each, refer to "PLL Configuration Bits Description" on page 106. The configuration register can be serially loaded with the new configuration data and programmed into the CCC using the following ports:

- SDIN: The configuration bits are serially loaded into a shift register through this port. The LSB of the configuration data bits should be loaded first.
- SDOUT: The shift register contents can be shifted out (LSB first) through this port using the shift operation.
- SCLK: This port should be driven by the shift clock.
- SSHIFT: The active-high shift enable signal should drive this port. The configuration data will be shifted into the shift register if this signal is HIGH. Once SSHIFT goes LOW, the data shifting will be halted.
- SUPDATE: The SUPDATE signal is used to configure the CCC with the new configuration bits when shifting is complete.

To access the configuration ports of the shift register (SDIN, SDOUT, SSHIFT, etc.), the user should instantiate the CCC macro in his design with appropriate ports. Microsemi recommends that users choose SmartGen to generate the CCC macros with the required ports for dynamic reconfiguration.

Users must familiarize themselves with the architecture of the CCC core and its input, output, and configuration ports to implement the desired delay and output frequency in the CCC structure. Figure 4-22 shows a model of the CCC with configurable blocks and switches.

Table 4-18 **• Fusion Dynamic CCC Division by Half Configuration**

OADIVHALF / OBDIVHALF / OCDIVHALF	OADIV<4:0> / OBDIV<4:0> / OCDIV<4:0> (in decimal)	Divider Factor	Input Clock Frequency	Output Clock Frequency (MHz)
1	2	1.5	100 MHz RC Oscillator	66.7
	4	2.5		40.0
	6	3.5		28.6
	8	4.5		22.2
	10	5.5		18.2
	12	6.5		15.4
	14	7.5		13.3
	16	8.5		11.8
	18	9.5		10.5
	20	10.5		9.5
	22	11.5		8.7
	24	12.5		8.0
	26	13.5		7.4
	28	14.5		6.9
0	0–31	1–32	Other Clock Sources	Depends on other divider settings

Table 4-19 **• Configuration Bit <76:75> / VCOSEL<2:1> Selection for All Families**

Voltage	VCOSEL[2:1]							
	00		01		10		11	
	Min. (MHz)	Max. (MHz)	Min. (MHz)	Max. (MHz)	Min. (MHz)	Max. (MHz)	Min. (MHz)	Max. (MHz)
IGLOO and IGLOO PLUS								
1.2 V ± 5%	24	35	30	70	60	140	135	160
1.5 V ± 5%	24	43.75	30	87.5	60	175	135	250
ProASIC3L, RT ProASIC3, and Military ProASIC3/L								
1.2 V ± 5%	24	35	30	70	60	140	135	250
1.5 V ± 5%	24	43.75	30	70	60	175	135	350
ProASIC3 and Fusion								
1.5 V ± 5%	24	43.75	33.75	87.5	67.5	175	135	350

Table 4-20 **• Configuration Bit <74> / VCOSEL<0> Selection for All Families**

VCOSEL[0]	Description
0	Fast PLL lock acquisition time with high tracking jitter. Refer to the corresponding datasheet for specific value and definition.
1	Slow PLL lock acquisition time with low tracking jitter. Refer to the corresponding datasheet for specific value and definition.

```
    wire VCC, GND;

    VCC VCC_1_net(.Y(VCC));
    GND GND_1_net(.Y(GND));
    PLL Core(.CLKA(CLKA), .EXTFB(GND), .POWERDOWN(POWERDOWN),
        .GLA(GLA), .LOCK(LOCK), .GLB(), .YB(), .GLC(), .YC(),
        .OADIV0(GND), .OADIV1(GND), .OADIV2(GND), .OADIV3(GND),
        .OADIV4(GND), .OAMUX0(GND), .OAMUX1(GND), .OAMUX2(VCC),
        .DLYGLA0(GND), .DLYGLA1(GND), .DLYGLA2(GND), .DLYGLA3(GND)
        , .DLYGLA4(GND), .OBDIV0(GND), .OBDIV1(GND), .OBDIV2(GND),
        .OBDIV3(GND), .OBDIV4(GND), .OBMUX0(GND), .OBMUX1(GND),
        .OBMUX2(GND), .DLYYB0(GND), .DLYYB1(GND), .DLYYB2(GND),
        .DLYYB3(GND), .DLYYB4(GND), .DLYGLB0(GND), .DLYGLB1(GND),
        .DLYGLB2(GND), .DLYGLB3(GND), .DLYGLB4(GND), .OCDIV0(GND),
        .OCDIV1(GND), .OCDIV2(GND), .OCDIV3(GND), .OCDIV4(GND),
        .OCMUX0(GND), .OCMUX1(GND), .OCMUX2(GND), .DLYYC0(GND),
        .DLYYC1(GND), .DLYYC2(GND), .DLYYC3(GND), .DLYYC4(GND),
        .DLYGLC0(GND), .DLYGLC1(GND), .DLYGLC2(GND), .DLYGLC3(GND)
        , .DLYGLC4(GND), .FINDIV0(VCC), .FINDIV1(GND), .FINDIV2(
        VCC), .FINDIV3(GND), .FINDIV4(GND), .FINDIV5(GND),
        .FINDIV6(GND), .FBDIV0(VCC), .FBDIV1(GND), .FBDIV2(VCC),
        .FBDIV3(GND), .FBDIV4(GND), .FBDIV5(GND), .FBDIV6(GND),
        .FBDLY0(GND), .FBDLY1(GND), .FBDLY2(GND), .FBDLY3(GND),
        .FBDLY4(GND), .FBSEL0(VCC), .FBSEL1(GND), .XDLYSEL(GND),
        .VCOSEL0(GND), .VCOSEL1(GND), .VCOSEL2(GND));
    defparam Core.VCOFREQUENCY = 33.000;
endmodule
```

The "PLL Configuration Bits Description" section on page 106 provides descriptions of the PLL configuration bits for completeness. The configuration bits are shown as busses only for purposes of illustration. They will actually be broken up into individual pins in compilation libraries and all simulation models. For example, the FBSEL[1:0] bus will actually appear as pins FBSEL1 and FBSEL0. The setting of these select lines for the static PLL configuration is performed by the software and is completely transparent to the user.

Simulation of FlashROM Design

The MEM file has 128 rows of 8 bits, each representing the contents of the FlashROM used for simulation. For example, the first row represents page 0, byte 0; the next row is page 0, byte 1; and so the pattern continues. Note that the three MSBs of the address define the page number, and the four LSBs define the byte number. So, if you send address 0000100 to FlashROM, this corresponds to the page 0 and byte 4 location, which is the fifth row in the MEM file. SmartGen defaults to 0s for any unspecified location of the FlashROM. Besides using the MEM file generated by SmartGen, you can create a binary file with 128 rows of 8 bits each and use this as a MEM file. Microsemi recommends that you use different file names if you plan to generate multiple MEM files. During simulation, Libero SoC passes the MEM file used as the generic file in the netlist, along with the design files and testbench. If you want to use different MEM files during simulation, you need to modify the generic file reference in the netlist.

```
....................
UFROM0: UFROM
--generic map(MEMORYFILE => "F:\Appsnotes\FROM\test_designs\testa\smartgen\FROM_a.mem")
--generic map(MEMORYFILE => "F:\Appsnotes\FROM\test_designs\testa\smartgen\FROM_b.mem")
.......................
```

The VITAL and Verilog simulation models accept the generics passed by the netlist, read the MEM file, and perform simulation with the data in the file.

Programming File Generation for FlashROM Design

FlashPoint is the programming software used to generate the programming files for flash devices. Depending on the applications, you can use the FlashPoint software to generate a STAPL file with different FlashROM contents. In each case, optional AES decryption is available. To generate a STAPL file that contains the same FPGA core content and different FlashROM contents, the FlashPoint software needs an Array Map file for the core and UFC file(s) for the FlashROM. This final STAPL file represents the combination of the logic of the FPGA core and FlashROM content.

FlashPoint generates the STAPL files you can use to program the desired FlashROM page and/or FPGA core of the FPGA device contents. FlashPoint supports the encryption of the FlashROM content and/or FPGA Array configuration data. In the case of using the FlashROM for device serialization, a sequence of unique FlashROM contents will be generated. When generating a programming file with multiple unique FlashROM contents, you can specify in FlashPoint whether to include all FlashROM content in a single STAPL file or generate a different STAPL file for each FlashROM (Figure 5-11). The programming software (FlashPro) handles the single STAPL file that contains the FlashROM content from multiple devices. It enables you to program the FlashROM content into a series of devices sequentially (Figure 5-11). See the *FlashPro User's Guide* for information on serial programming.

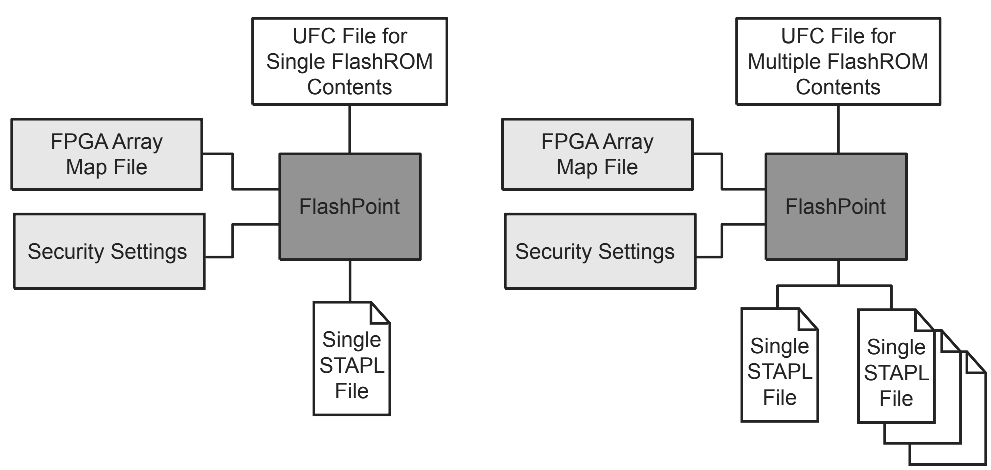


***Figure 5-11* • Single or Multiple Programming File Generation**

I/O Bank Structure

Low power flash device I/Os are divided into multiple technology banks. The number of banks is device-dependent. The IGLOOe, ProASIC3EL, and ProASIC3E devices have eight banks (two per side); and IGLOO, ProASIC3L, and ProASIC3 devices have two to four banks. Each bank has its own V**CCI** power supply pin. Multiple I/O standards can co-exist within a single I/O bank.

In IGLOOe, ProASIC3EL, and ProASIC3E devices, each I/O bank is subdivided into VREF minibanks. These are used by voltage-referenced I/Os. VREF minibanks contain 8 to 18 I/Os. All I/Os in a given minibank share a common VREF line (only one VREF pin is needed per VREF minibank). Therefore, if an I/O in a VREF minibank is configured as a VREF pin, the remaining I/Os in that minibank will be able to use the voltage assigned to that pin. If the location of the VREF pin is selected manually in the software, the user must satisfy VREF rules (refer to the "I/O Software Control in Low Power Flash Devices" section on page 251). If the user does not pick the VRE_F pin manually, the software automatically assigns it.

Figure 7-3 is a snapshot of a section of the I/O ring, showing the basic elements of an I/O tile, as viewed from the Designer place-and-route tool's MultiView Navigator (MVN).

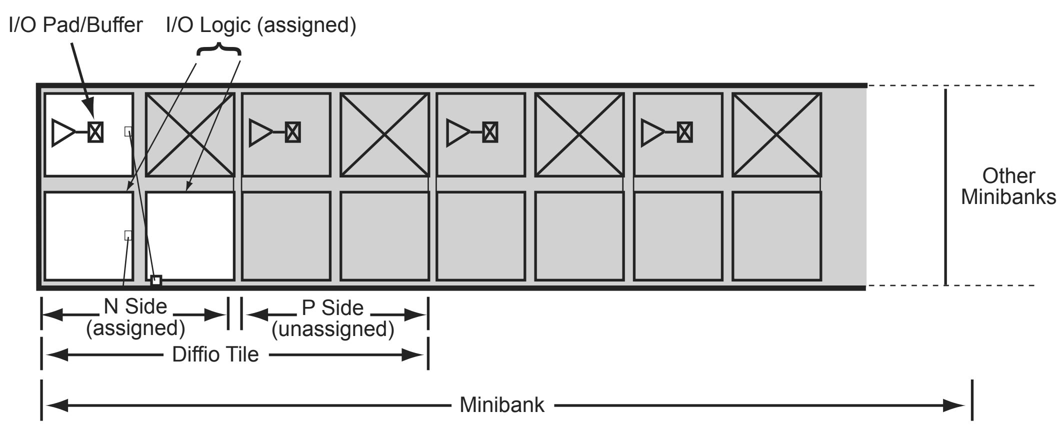


Figure 7-3 • **Snapshot of an I/O Tile**

Low power flash device I/Os are implemented using two tile types: I/O and differential I/O (diffio).

The diffio tile is built up using two I/O tiles, which form an I/O pair (P side and N side). These I/O pairs are used according to differential I/O standards. Both the P and N sides of the diffio tile include an I/O buffer and two I/O logic blocks (auxiliary and main logic).

Every minibank (E devices only) is built up from multiple diffio tiles. The number of the minibank depends on the different-size dies. Refer to the "I/O Architecture" section on page 181 for an illustration of the minibank structure.

Figure 7-4 on page 183 shows a simplified diagram of the I/O buffer circuitry. The Output Enable signal (OE) enables the output buffer to pass the signal from the core logic to the pin. The output buffer contains ESD protection circuitry, an n-channel transistor that shunts all ESD surges (up to the limit of the device ESD specification) to GND. This transistor also serves as an output pull-down resistor.

Each output buffer also contains programmable slew rate, drive strength, programmable power-up state (pull-up/-down resistor), hot-swap, 5 V tolerance, and clamp diode control circuitry. Multiple flash switches (not shown in Figure 7-4 on page 183) are programmed by user selections in the software to activate different I/O features.

GTL+ (Gunning Transceiver Logic Plus)

This is an enhanced version of GTL that has defined slew rates and higher voltage levels. It requires a differential amplifier input buffer and an open-drain output buffer. Even though the output is open-drain, VCCI must be connected to either 2.5 V or 3.3 V. The reference voltage (VREF) is 1 V.

Differential Standards

These standards require two I/Os per signal (called a “signal pair”). Logic values are determined by the potential difference between the lines, not with respect to ground. This is why differential drivers and receivers have much better noise immunity than single-ended standards. The differential interface standards offer higher performance and lower power consumption than their single-ended counterparts. Two I/O pins are used for each data transfer channel. Both differential standards require resistor termination.

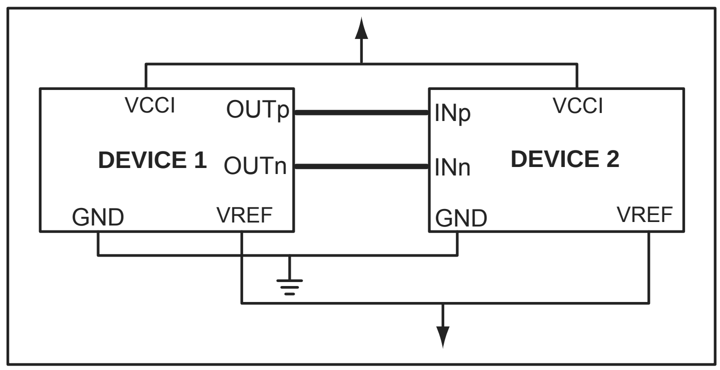


Figure 7-7 • **Differential Topology**

LVPECL (Low-Voltage Positive Emitter Coupled Logic)

LVPECL requires that one data bit be carried through two signal lines; therefore, two pins are needed per input or output. It also requires external resistor termination. The voltage swing between the two signal lines is approximately 850 mV. When the power supply is +3.3 V, it is commonly referred to as Low-Voltage PECL (LVPECL). Refer to the device datasheet for the full implementation of the LVPECL transmitter and receiver.

LVDS (Low-Voltage Differential Signal)

LVDS is a moderate-speed differential signaling system, in which the transmitter generates two different voltages that are compared at the receiver. LVDS uses a differential driver connected to a terminated receiver through a constant-impedance transmission line. It requires that one data bit be carried through two signal lines; therefore, the user will need two pins per input or output. It also requires external resistor termination. The voltage swing between the two signal lines is approximately 350 mV. VCCI is 2.5 V. Low power flash devices contain dedicated circuitry supporting a high-speed LVDS standard that has its own user specification. Refer to the device datasheet for the full implementation of the LVDS transmitter and receiver.

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) refers to bus interface circuits based on LVDS technology. Multipoint LVDS (M-LVDS) specifications extend the LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The driver requires series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus, since the driver can be located anywhere on the bus. These configurations can be implemented using TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 7-8. The input and output buffer delays are available in the LVDS sections in the datasheet.

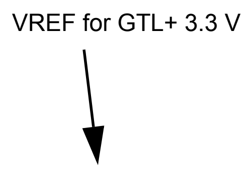


Figure 9-13 **• Selecting VREF Voltage for the I/O Bank**

Assigning VREF Pins for a Bank

The user can use default pins for VREF. In this case, select the **Use default pins for VREFs** check box (Figure 9-13). This option guarantees full VREF coverage of the bank. The equivalent PDC command is as follows:

```
set_vref_default [bank name]
```

To be able to choose VREF pins, adequate VREF pins must be created to allow legal placement of the compatible voltage-referenced I/Os.

To assign VREF pins manually, the PDC command is as follows:

```
set_vref –bank [bank name] [package pin numbers]
```

For ChipPlanner/PinEditor to show the range of a VREF pin, perform the following steps:

1. Assign VCCI to a bank using **MVN** > **Edit** > **I/O Bank Settings**.
2. Open **ChipPlanner**. Zoom in on an I/O package pin in that bank.
3. Highlight the pin and then right-click. Choose **Use Pin for VREF**.

Input Support for DDR

The basic structure to support a DDR input is shown in Figure 10-2. Three input registers are used to capture incoming data, which is presented to the core on each rising edge of the I/O register clock. Each I/O tile supports DDR inputs.

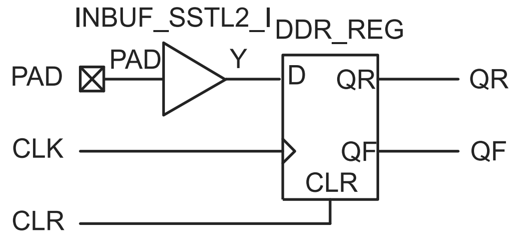


Figure 10-2 **• DDR Input Register Support in Low Power Flash Devices**

Output Support for DDR

The basic DDR output structure is shown in Figure 10-1 on page 271. New data is presented to the output every half clock cycle.

Note: DDR macros and I/O registers do not require additional routing. The combiner automatically recognizes the DDR macro and pushes its registers to the I/O register area at the edge of the chip. The routing delay from the I/O registers to the I/O buffers is already taken into account in the DDR macro.

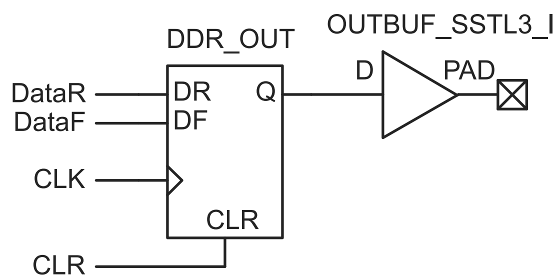


Figure 10-3 **• DDR Output Register (SSTL3 Class I)**

Programming Solutions

Details for the available programmers can be found in the programmer user's guides listed in the "Related Documents" section on page 297.

All the programmers except FlashPro4, FlashPro3, FlashPro Lite, and FlashPro require adapter modules, which are designed to support device packages. All modules are listed on the Microsemi SoC Products Group website at http://www.microsemi.com/soc/products/hardware/program_debug/ss/modules.aspx. They are not listed in this document, since this list is updated frequently with new package options and any upgrades required to improve programming yield or support new families.

Table 11-3 **• Programming Solutions**

Programmer	Vendor	ISP	Single Device	Multi-Device	Availability
FlashPro4	Microsemi	Only	Yes	Yes[1]	Available
FlashPro3	Microsemi	Only	Yes	Yes[1]	Available
FlashPro Lite[2]	Microsemi	Only	Yes	Yes[1]	Available
FlashPro	Microsemi	Only	Yes	Yes[1]	Discontinued
Silicon Sculptor 3	Microsemi	Yes[3]	Yes	Cascade option (up to two)	Available
Silicon Sculptor II	Microsemi	Yes[3]	Yes	Cascade option (up to two)	Available
Silicon Sculptor	Microsemi	Yes	Yes	Cascade option (up to four)	Discontinued
Sculptor 6X	Microsemi	No	Yes	Yes	Discontinued
BP MicroProgrammers	BP Microsystems	No	Yes	Yes	Contact BP Microsystems at www.bpmicro.com

Notes:

1. *Multiple devices can be connected in the same JTAG chain for programming.*
2. *If FlashPro Lite is used for programming, the programmer derives all of its power from the target pc board's VDD supply. The FlashPro Lite's VPP and VPN power supplies use the target pc board's VDD as a power source. The target pc board must supply power to both the VDDP and VDD power pins of the ProASIC^{PLUS} device in addition to supplying VDD to the FlashPro Lite. The target pc board needs to provide at least 500 mA of current to the FlashPro Lite VDD connection for programming.*
3. *Silicon Sculptor II and Silicon Sculptor 3 can only provide ISP for ProASIC and ProASIC^{PLUS} families, not for Fusion, IGLOO, or ProASIC3 devices.*

FlashROM Security Use Models

Each of the subsequent sections describes in detail the available selections in Microsemi Designer as an aid to understanding security applications and generating appropriate programming files for those applications. Before proceeding, it is helpful to review Figure 12-7 on page 309, which gives a general overview of the programming file generation flow within the Designer software as well as what occurs during the device programming stage. Specific settings are discussed in the following sections.

In Figure 12-7 on page 309, the flow consists of two sub-flows. Sub-flow 1 describes programming security settings to the device only, and sub-flow 2 describes programming the design contents only.

In Application 1, described in the "Application 1: Trusted Environment" section on page 309, the user does not need to generate separate files but can generate one programming file containing both security settings and design contents. Then programming of the security settings and design contents is done in one step. Both sub-flow 1 and sub-flow 2 are used.

In Application 2, described in the "Application 2: Nontrusted Environment—Unsecured Location" section on page 309, the trusted site should follow sub-flows 1 and 2 separately to generate two separate programming files. The programming file from sub-flow 1 will be used at the trusted site to program the device(s) first. The programming file from sub-flow 2 will be sent off-site for production programming.

In Application 3, described in the "Application 3: Nontrusted Environment—Field Updates/Upgrades" section on page 310, typically only sub-flow 2 will be used, because only updates to the design content portion are needed and no security settings need to be changed.

In the event that update of the security settings is necessary, see the "Reprogramming Devices" section on page 321 for details. For more information on programming low power flash devices, refer to the "In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" section on page 327.

errors, but this list is intended to show where problems can occur. FlashPro4/3/3X allows TCK to be lowered from 6 MHz down to 1 MHz to allow you to address some signal integrity problems that may occur with impedance mismatching at higher frequencies. Customers are expected to troubleshoot board-level signal integrity issues by measuring voltages and taking scope plots.

Scan Chain Failure

Normally, the FlashPro4/3/3X Scan Chain command expects to see 0x1 on the TDO pin. If the command reports reading 0x0 or 0x3, it is seeing the TDO pin stuck at 0 or 1. The only time the TDO pin comes out of tristate is when the JTAG TAP state machine is in the Shift-IR or Shift-DR state. If noise or reflections on the TCK or TMS lines have disrupted the correct state transitions, the device's TAP state controller might not be in one of these two states when the programmer tries to read the device. When this happens, the output is floating when it is read and does not match the expected data value. This can also be caused by a broken TDO net. Only a small amount of data is read from the device during the Scan Chain command, so marginal problems may not always show up during this command. Occasionally a faulty programmer can cause intermittent scan chain failures.

Exit 11

This error occurs during the verify stage of programming a device. After programming the design into the device, the device is verified to ensure it is programmed correctly. The verification is done by shifting the programming data into the device. An internal comparison is performed within the device to verify that all switches are programmed correctly. Noise induced by poor signal integrity can disrupt the writes and reads or the verification process and produce a verification error. While technically a verification error, the root cause is often related to signal integrity.

Refer to the *FlashPro User's Guide* for other error messages and solutions. For the most up-to-date known issues and solutions, refer to http://www.microsemi.com/soc/support.

Conclusion

IGLOO, ProASIC3, SmartFusion, and Fusion devices offer a low-cost, single-chip solution that is live at power-up through nonvolatile flash technology. The FlashLock Pass Key and 128-bit AES Key security features enable secure ISP in an untrusted environment. On-chip FlashROM enables a host of new applications, including device serialization, subscription-based applications, and IP addressing. Additionally, as the FlashROM is nonvolatile, all of these services can be provided without battery backup.

Related Documents

User's Guides

FlashPro User's Guide

http://www.microsemi.com/soc/documents/flashpro_ug.pdf

Date	Changes	Page
July 2010 (continued)	The "Chain Integrity Test Error Analyze Chain Failure" section was renamed to the "Scan Chain Failure" section, and the Analyze Chain command was changed to Scan Chain. It was noted that occasionally a faulty programmer can cause scan chain failures.	338
v1.5 (August 2009)	The "CoreMP7 Device Security" section was removed from "Security in ARM-Enabled Low Power Flash Devices", since M7-enabled devices are no longer supported.	331
v1.4 (December 2008)	The "ISP Architecture" section was revised to include information about core voltage for IGLOO V2 and ProASIC3L devices, as well as 50 mV increments allowable in Designer software.	327
	IGLOO nano and ProASIC3 nano devices were added to Table 13-1 • Flash-Based FPGAs Supporting ISP.	328
	A second capacitor was added to Figure 13-6 • Board Layout and Programming Header Top View.	337
v1.3 (October 2008)	The "ISP Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	328
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 13-1 • Flash-Based FPGAs Supporting ISP: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	328
v1.1 (March 2008)	The "ISP Architecture" section was updated to included the IGLOO PLUS family in the discussion of family-specific support. The text, "When 1.2 V is used, the device can be reprogrammed in-system at 1.5 V only," was revised to state, "Although the device can operate at 1.2 V core voltage, the device can only be reprogrammed when all supplies (VCC, VCCI, and VJTAG) are at 1.5 V."	327
	The "ISP Support in Flash-Based Devices" section and Table 13-1 • Flash-Based FPGAs Supporting ISP were updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	328
	The "Security" section was updated to mention that 15 k gate devices do not have a built-in 128-bit decryption core.	330
	Table 13-2 • Power Supplies was revised to remove the Normal Operation column and add a table note stating, "All supply voltages should be at 1.5 V or higher, regardless of the setting during normal operation."	329
	The "ISP Programming Header Information" section was revised to change FP3-26PIN-ADAPTER to FP3-10PIN-ADAPTER-KIT. Table 13-3 • Programming Header Ordering Codes was updated with the same change, as well as adding the part number FFSD-05-D-06.00-01-N, a 10-pin cable with 50-mil-pitch sockets.	335
	The "Board-Level Considerations" section was updated to describe connecting two capacitors in parallel across VPUMP and GND for proper programming.	337
v1.0 (January 2008)	Information was added to the "Programming Voltage (VPUMP) and VJTAG" section about the JTAG interface pin.	329
51900055-2/7.06	ACTgen was changed to SmartGen.	N/A
	In Figure 13-6 • Board Layout and Programming Header Top View, the order of the text was changed to: VJTAG from the target board VCCI from the target board VCC from the target board	337

UJTAG Support in Flash-Based Devices

The flash-based FPGAs listed in Table 17-1 support the UJTAG feature and the functions described in this document.

Table 17-1 **• Flash-Based FPGAs**

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

Note: **The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.*

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 17-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 17-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.